
2SC5250

Silicon NPN Triple Diffused Planar

HITACHI

Preliminary

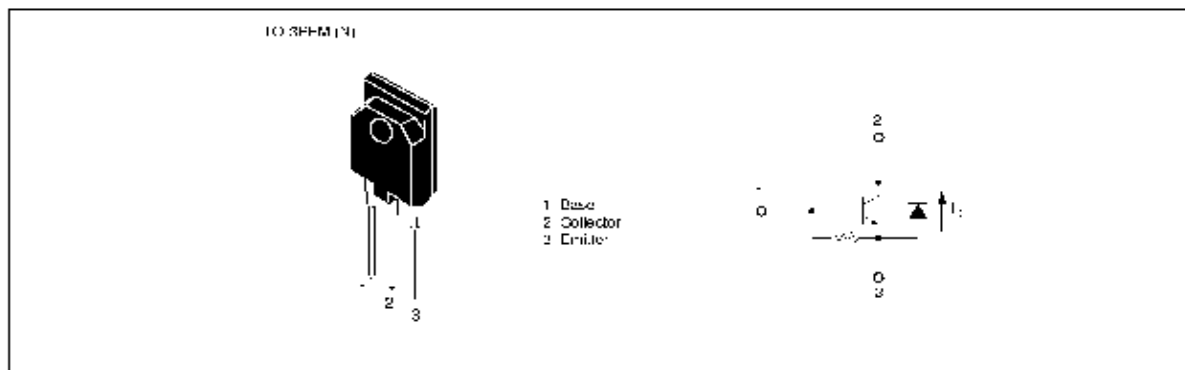
Application

Character display horizontal deflection output

Features

- High breakdown voltage
 $V_{CEO} = 1500 \text{ V}$
- High speed switching
 $t_L = 0.2 \mu\text{sec (typ)}$
- Built-in damper diode type
- Isolated package
TO-3P•TM (N)

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to emitter voltage	V_{CE2}	1500	V
Emitter to base voltage	V_{EB2}	6	V
Collector current	I_C	8	A
Collector peak current	$I_{C(pk)}$	16	A
Collector power dissipation	P_C^*	50	W
Junction temperature	T_J	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
Diode current	I_D	8	A

Note: 1. Value at $T_J = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Emitter to base breakdown voltage	$V_{(BR)EB}$	6	—	—	V	$I_E = 400\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CE2}	—	—	500	μA	$V_{CE} = 1500\text{ V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE}	6	—	25		$V_{CE} = 5\text{ V}$, $I_C = 1\text{ A}$
DC current transfer ratio	h_{FE2}	4	—	7		$V_{CE} = 5\text{ V}$, $I_C = 5\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 5\text{ A}$, $I_E = 1.25\text{ A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 5\text{ A}$, $I_E = 1.25\text{ A}$
Forward voltage of damper diode	V_F	—	—	2	V	$I_F = 8\text{ A}$
Fall time	t_f	—	0.2	0.4	μsec	$I_{C2} = 5\text{ A}$, $I_{B1} = 1\text{ A}$, $f_c = 31.5\text{ kHz}$

